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**Claim Amendments**

Please amend claims 1, 11, and 12 as follows:

**Claims as Amended**

1. (currently amended) A method of removing defects in a back-end photomask making process, comprising the steps of:

(a) searching for a defect on a photomask with a mask marking inspection system, the mark masking inspection system including a photomask inspection apparatus and a mark installer linked with the photomask inspection apparatus;

(b) disposing a defect finder mark on the photomask patterened portion with the mark installer;

(c) repairing the defect, and

(d) eliminating the defect finder mark.

2. (Original) The method according to claim 1 wherein the step of searching for a defect on a photomask includes the step of locating a defect on the photomask.

3. (Original) The method according to claim 1 wherein the step

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of searching for a defect includes the step for searching for the defect about a dense pattern array of the photomask.

4. (Original) The method according to the claim 1 wherein the step of searching for a defect includes the step of searching for an elusive defect.

5. (Original) The method according to claim 1 wherein the step of disposing a defect finder mark on the photomask includes the step of establishing a location of the defect finder mark that is adjacent to the defect.

6. (Original) The method according to claim 1 wherein the step of disposing a defect finder mark on the photomask includes the step of establishing a size for the defect finder mark so that the defect finder mark is detected with a mask repair device.

7. (Original) The method according to claim 1 further comprising the step of searching for the defect finder mark on the photomask with the mask repair device.

8. - 9. (Canceled)

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10. (previously presented) The method according to claim 1 wherein the step of eliminating the defect finder mark includes depositing a filling agent on the defect finder mark.

11. (currently amended) The method according to claim [[9]] 1 further including the step of forming a photoresist image on a wafer substrate with the photomask.

12. (currently amended) A back-end method for photomask making, comprising the steps of:

(a) inspecting a photomask, said inspecting including the steps of searching for a defect on the photomask with a mask marking inspection system, the mask marking inspection system including a photomask inspection apparatus and a mark installer linked with a photomask inspection apparatus, and disposing a defect finder mark on the photomask patterned portion with the mark installer;

(b) repairing the defect on the photomask; and

(c) eliminating the defect finder mark from the photomask.

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13. (Original) The back-end method according to claim 12 further comprising the step of cleaning the photomask.

14. (Original) The back-end method according to claim 12 further comprising the step of applying pellicle to the photomask.

15. (Original) The back-end method according to claim 12 wherein the step for searching for a defect includes the step for searching for the defect about a dense pattern array of the photomask.

16. (Original) The back-end method according to claim 12 wherein the step of searching for a defect includes the step of searching for an elusive defect.

17. (Original) The back-end method according to claim 12 wherein the step of disposing a defect finder mark on the photomask includes the step of establishing a location of the defect finder mark that is adjacent to the defect.

18. (Original) The back-end method according to claim 12 wherein the step of disposing a defect finder mark on the photomask includes the step of establishing a size for the defect finder

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mark so that the defect finder mark is detected with a mask repair device.

19. (Original) The back-end method according to claim 12 further comprising the step of searching for the defect finder mark on the photomask with the mask repair device.

20. (Canceled)